

ABSTRACT OF THE DISCLOSURE

A method of forming a micromechanical structure. A first sacrificial silicon layer is formed on a substrate. A mirror plate is formed on part of the first sacrificial silicon layer. Argon sputtering is performed on the mirror plate and the first sacrificial silicon layer. A hydrogen treatment is performed on the first sacrificial silicon layer to form an H-treated silicon surface thereon. A second sacrificial silicon layer is formed over the mirror plate and the first sacrificial silicon layer. At least one hole is formed to penetrate the second sacrificial silicon layer, the mirror plate and the first sacrificial silicon layer. A conductive material fills in the hole to define a mirror support structure attached to the mirror plate and the substrate. The first and second sacrificial layers are removed to release the mirror plate.